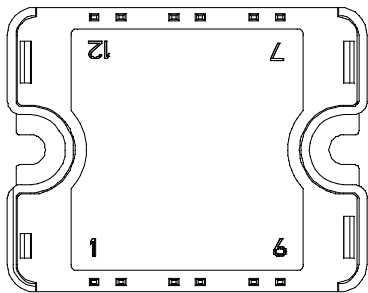
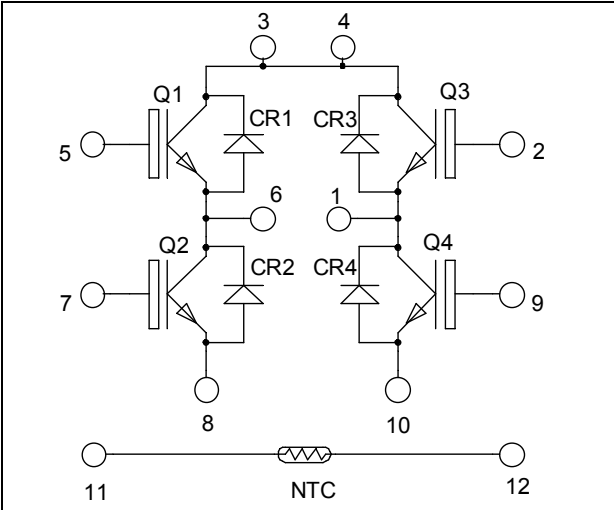


Full - Bridge
High speed Trench + Field Stop
IGBT4 Power Module

$V_{CES} = 1200V$
 $I_C = 25A @ T_c = 80^\circ C$



Pins 3/4 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- **High speed Trench + Field Stop IGBT 4 Technology**
 - Low voltage drop
 - Low leakage current
 - Low switching losses
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	50
		$T_c = 80^\circ C$	25
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	100
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Power Dissipation	165	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _{CEs}	Zero Gate Voltage Collector Current	V _{GE} = 0V, V _{CE} = 1200V			50	μA
V _{CE(sat)}	Collector Emitter Saturation Voltage	V _{GE} = 15V I _C = 25A	1.78	2.05	2.42	V
		T _j = 25°C T _j = 150°C		2.6		
V _{GE(th)}	Gate Threshold Voltage	V _{GE} = V _{CE} , I _C = 0.85 mA	5.3	5.8	6.3	V
I _{GES}	Gate – Emitter Leakage Current	V _{GE} = 20V, V _{CE} = 0V			150	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{ies}	Input Capacitance	V _{GE} = 0V V _{CE} = 25V f = 1MHz		1430		pF
C _{oes}	Output Capacitance			95		
C _{res}	Reverse Transfer Capacitance			75		
Q _G	Gate charge	V _{GE} = 15V, I _C = 25A V _{CE} = 960V		115		nC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{GE} = ±15V V _{Bus} = 600V I _C = 25A R _G = 19Ω		27		ns
T _r	Rise Time			41		
T _{d(off)}	Turn-off Delay Time			277		
T _f	Fall Time			17		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) V _{GE} = ±15V V _{Bus} = 600V I _C = 25A R _G = 19Ω		26		ns
T _r	Rise Time			35		
T _{d(off)}	Turn-off Delay Time			347		
T _f	Fall Time			50		
E _{on}	Turn on Energy	V _{GE} = ±15V V _{Bus} = 600V I _C = 25A		2.4		mJ
E _{off}	Turn off Energy	R _G = 19Ω		1.4		
I _{sc}	Short Circuit data	V _{GE} ≤ 15V ; V _{Bus} = 600V t _p ≤ 10μs ; T _j = 150°C		90		A
R _{thJC}	Junction to Case Thermal Resistance				0.9	°C/W

Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage				1200	V
I _{RM}	Reverse Leakage Current	V _R = 1200V			100	μA
I _F	DC Forward Current	T _c = 80°C		30		A
V _F	Diode Forward Voltage	I _F = 30A		2.6	3.1	V
		I _F = 60A		3.2		
		I _F = 30A	T _j = 125°C		1.8	
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 800V di/dt = 200A/μs	T _j = 25°C		300	ns
			T _j = 125°C		380	
Q _{rr}	Reverse Recovery Charge	I _F = 30A V _R = 800V di/dt = 200A/μs	T _j = 25°C		360	nC
			T _j = 125°C		1700	
R _{thJC}	Junction to Case Thermal Resistance				1.2	°C/W

Thermal and package characteristics

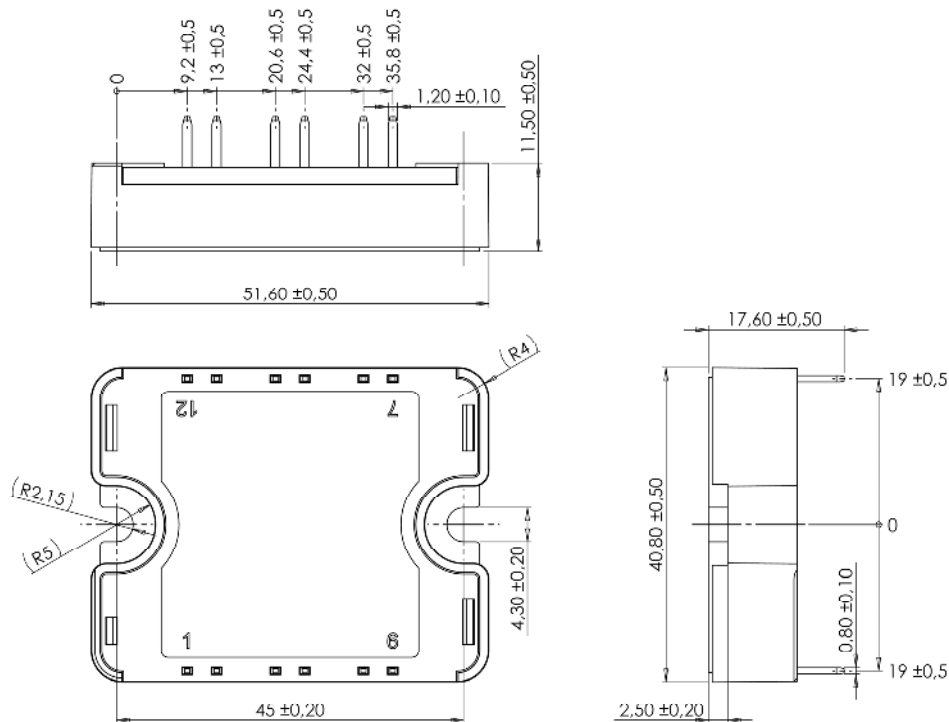
Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000		V		
T _J	Operating junction temperature range	-40	175	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage Temperature Range	-40	125			
T _C	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

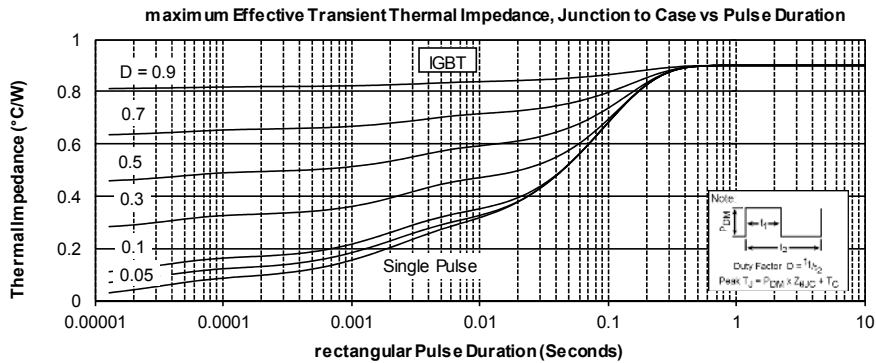
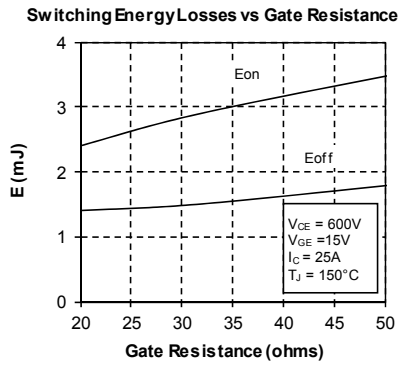
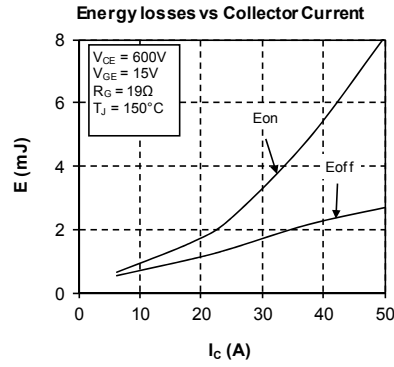
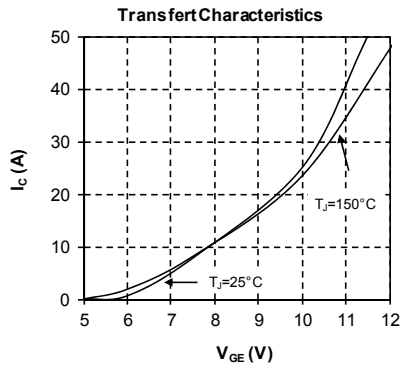
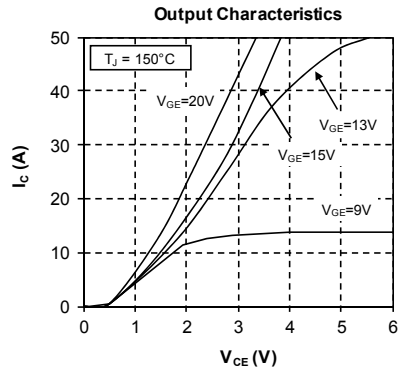
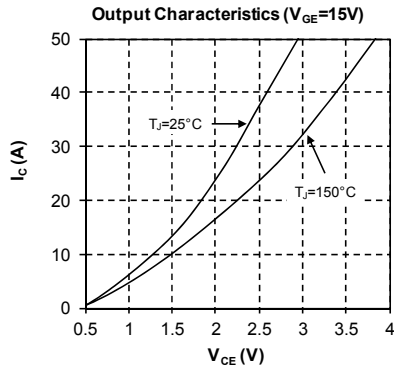
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

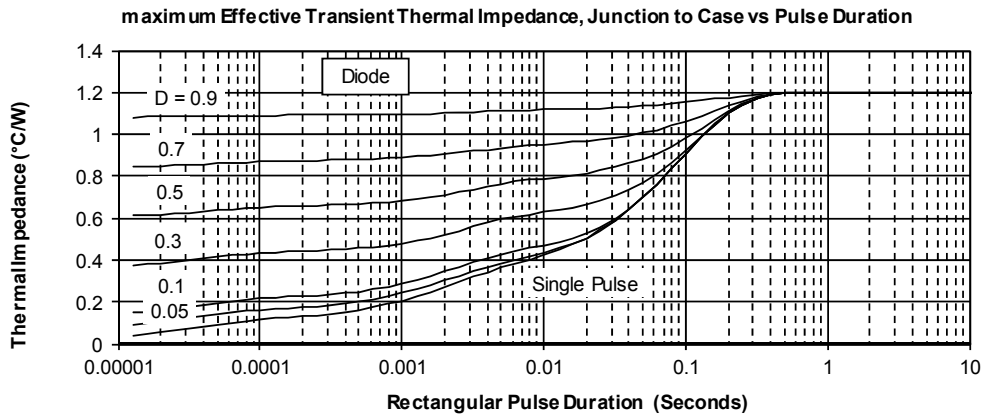
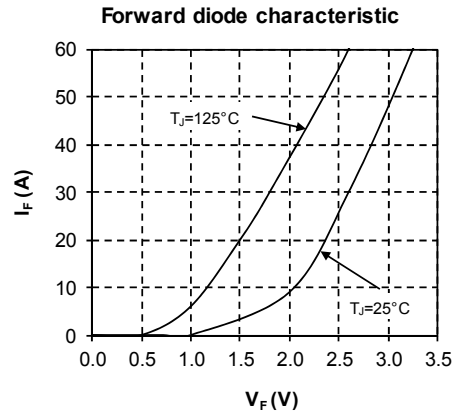
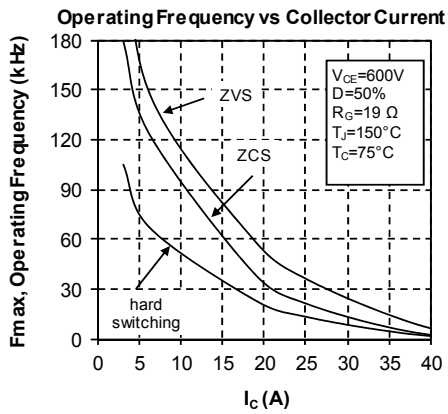
T: Thermistor temperature
 R_T: Thermistor value at T

Package outline (dimensions in mm)


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Typical Performance Curve





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